INFORMATION DISCLOSURE CITATION PTO-1449	Customer Number: 26615	ATTORNEY'S DKT NO. H1420	APPLICATION NO. ~~Unassigned~~ 10/754559
		APPLICANT(S) Shibly S. Ahmed et al.	
		FILING DATE January 12, 2004	GROUP ~~Unassigned~~ 2818

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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	6,583,469	06-24-03	Fried et al.	257	329	01-28-02
	6,562,665	05-13-03	Yu	438	149	10-16-00
	6,551,886	04-22-03	Yu	438	300	04-27-01

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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes	Translation No
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	Digh Hisamoto et al., "FinFET-A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.
	Yang-Kyu Choi et al., "Sub-20nm CMOS FinFET Technologies," 2001 IEEE, IEDM, pages 421-424.
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	Co-pending U.S. Application No. 10/320,536 filed December 17, 2002 entitled: "FinFET Gate Formation Using Reverse Trim of Dummy Gate," 14 page specification, 11 sheets of drawings.
	Co-pending U.S. Application No.10/459,589 filed June 12, 2003 entitled: "FinFET Gate Formation Using Reverse Trim and Oxide Polish," 17 page specification, 28 sheets of drawings.
	Co-pending U.S. Application No. 10/310,777 filed December 6, 2002 entitled: "Damascene Gate Process with Sacrificial Oxide in Semiconductor Devices," 19 page specification, 10sheets of drawings.
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EXAMINER	DATE CONSIDERED 7/16/05

INFORMATION DISCLOSURE CITATION PTO-1449	Customer Number: 26615	ATTORNEY'S DKT NO. H1420	APPLICATION NO. ~~Unassigned~~ 10/754,559
		APPLICANT(S) Shibly S. Ahmed et al.	
		FILING DATE January 12, 2004	GROUP Unassigned

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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
TL	6,551,885	04-22-03	Yu	438	300	02-09-01
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TL	6,406,951	06-18-02	Yu	438	183	02-12-01
TL	6,342,410	01-29-02	Yu	438	164	07-10-00
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TL	6,265,256	07-24-01	An et al.	438	201	09-17-98
TL	5,960,270	09-28-99	Misra et al.	438	197	08-11-97
TL	US2003/01581077	08-14-03	Mathew et al.	257	250	02-13-02
TL	US2003/0141525	07-31-03	Nowak	257	288	02-05-03
TL	US2003/0113970	06-19-03	Fried et al.	438	286	12-14-01
TL	US2003/0111686	06-19-03	Nowak	257	328	12-13-01

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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes	Translation No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	DATE CONSIDERED
[signature]	7/16/05

INFORMATION DISCLOSURE CITATION PTO-1449	CUSTOMER NUMBER 45114	ATTORNEY'S DKT NO. H1420	APPLICATION NO. 10/754,559
		APPLICANT(S) Shibly S. Ahmed et al.	
		FILING DATE January 12, 2004	GROUP 2812

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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
✓	6,764,884 B1	07/20/04	Yu et al.	438	157	
	6,465,823	10/15/02	Yagishita et al.	257	288	
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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes	Translation No
✓	EP 1 383 164 A1	01/21/04	Europe				

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✓	Copy of International Search Report dated March 4, 2005

EXAMINER	DATE CONSIDERED
[signature]	7/16/05

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INFORMATION DISCLOSURE CITATION PTO-1449	CUSTOMER NUMBER 26615	ATTORNEY'S DKT NO. H1420	APPLICATION NO. 10/754,559
		APPLICANT(S) Shibly S. Ahmed et al.	
		FILING DATE January 12, 2004	GROUP 2812

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
✓	6,396,108	05/28/02	Krivokapic et al.	257	365	
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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes	Translation No

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✓	Stephen H. Tang et al., "Comparison of Short-Channel Effect and Offstate Leakage in Symmetric vs. Asymmetric Double Gate MOSFETs", IEEE International SOI Conference, October 2000, pp. 120-121
✓	Co-pending U.S. Application No. 10/720,166 filed November 25, 2003 entitled: "Damascene Gate Process with Sacrificial Oxide in Semiconductor"; 19 page specification, 10 sheets of drawings.
✓	Co-pending U.S. Application No. 10/838,228 filed May 5, 2004 entitled: "Sacrificial Oxide for Minimizing Box Undercut in Damascene FinFet"; 15 page specification, 12 sheets of drawings.
✓	United States Patent Application Publication No. US2002/0153587; publication date October 24, 2002; Adkisson et al.

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	7/16/05

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		APPLICANT(S) Shibly S. Ahmed et al.	
		FILING DATE January 12, 2004	GROUP 2812

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
✓	6,645,797 B1	11/2003	Buynoski et al.	438	157	

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes	Translation No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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	7/16/05

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